



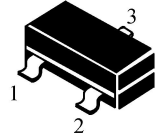
# 桂林斯壯桂微電子有限責任公司

## Guilin Strong Micro-Electronics Co.,Ltd.

GMBTA94(銷售型號 MMBTA94)

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



### FEATURES 特點

PNP High Voltage Transistor

### MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Emitter Voltage 集電極-射極電壓	$V_{CEO}$	-400	V
Collector-Base Voltage 集電極-基極電壓	$V_{CBO}$	-400	V
Emitter-Base Voltage 發射極基極電壓	$V_{EBO}$	-7	V
Collector Current 集電極電流	$I_c$	-200	mA
Device Dissipation 耗散功率	$P_D$	225	mW
Junction and Storage Temperature 結溫和儲存溫度	$T_J, T_{stg}$	-55to+125	°C

### ELECTRICAL CHARACTERISTICS 電特性

( $T_A=25^{\circ}C$  unless otherwise noted 如無特殊說明，溫度為  $25^{\circ}C$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Max 最大值	Unit 單位
Collector-Emitter Breakdown Voltage 集電極-射極擊穿電壓( $I_C=-1mA, I_B=0$ )	$V_{(BR)CEO}$	-400	—	V
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓( $I_C=-100\mu A, I_E=0$ )	$V_{(BR)CBO}$	-400	—	V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓( $I_E=-100\mu A, I_C=0$ )	$V_{(BR)EBO}$	-7	—	V
Collector Cutoff Current 集電極截止電流 ( $V_{CB}=-400V, I_E=0$ )	$I_{CBO}$	—	-500	nA
DC Current Gain 直流電流增益 ( $I_C=-10mA, V_{CE}=-10.0V$ )	$H_{FE}$	40	240	—
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降 ( $I_C=-20mA, I_B=-2mA$ )	$V_{CE(sat)}$	—	-0.6	V
Current-Gain-Bandwidth Product 電流增益帶寬乘積 ( $I_C=-10mA, V_{CE}=-20V, f=30MHz$ )	$f_T$	50	—	MHz

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■ **DEVICE MARKING 打標**

GMBTA94(銷售型號 MMBTA94)=4D

■ **TYPICAL CHARACTERISTIC CURVE 典型特性曲線**

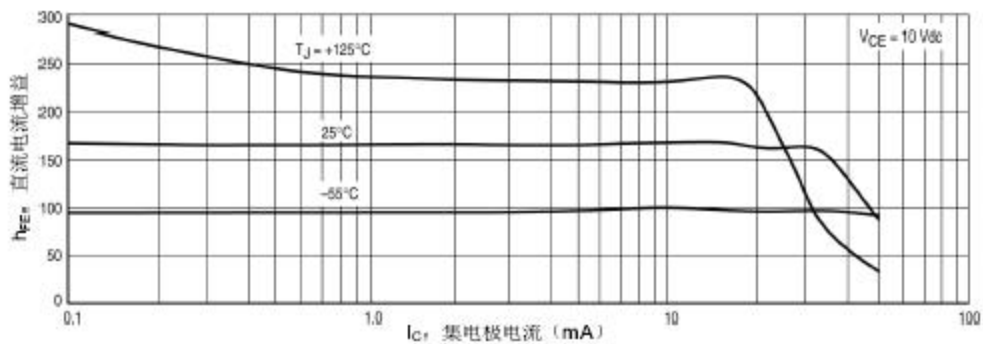


图 1. 直流电流增益

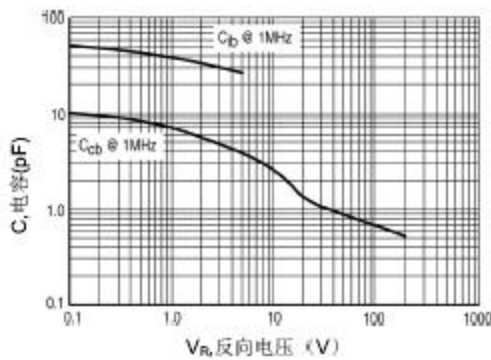


图 2. 电容

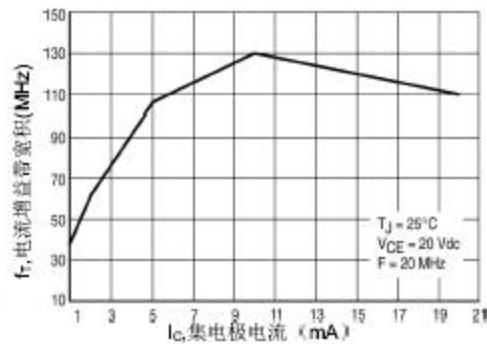


图 10. 电流增益带宽

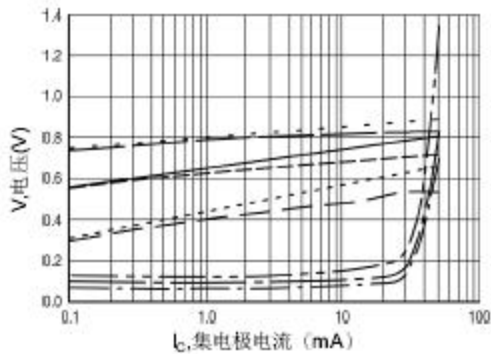


图 4. “导通”电压

- $V_{CE(sat)}$  @ 25°C,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @ 125°C,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @ -55°C,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @ 25°C,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @ 125°C,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @ -55°C,  $I_C/I_B = 10$
- $V_{BE(on)}$  @ 25°C,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @ 125°C,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @ -55°C,  $V_{CE} = 10\text{ V}$